*Thin Solid Films*, *177* (1989) vii–ix



## Contents

ELECTRONICS AND OPTICS

Influence of electrode material on the photocurrent in tantalum pentoxide films . . . . . 1
K. Miyairi (Nagano, Japan)

Tungsten silicide barrier layers in aluminium ohmic contact systems . . . . . 9
T. Hara, H. Hayashida, S. Takahashi and A. Yamanoue (Tokyo, Japan)

Electrical properties of sprayed tin oxide layers . . . . . 17
J. J. Ph. Elich, E. C. Boslooper and H. Haitjema (Delft, The Netherlands)

Anodic oxidation of tantalum in aqueous electrolytes . . . . . 35
K. C. Kalra, P. Katyal and K. C. Singh (Haryana, India)

A method for determining shape and volume of ellipsoidal silver particles from absorbance measurements . . . . . 49
J. P. Goudonnet, J. L. Bijeon and M. Pauty (Dijon, France)

Dielectric and optical properties of europium oxide films . . . . . 59
M. K. Jayaraj and C. P. G. Vallabhan (Cochin, India)

Theoretical optical properties of polar semiconductors used as optical coatings for energy-efficient windows . . . . . 69
Bo. E. Sernelius and M. Morling (Linköping, Sweden)

Structure and ammonia sensitivity of thin platinum or iridium gates in metal–oxide–silicon capacitors . . . . . 77
A. Spetz, U. Helmersson, F. Enquist, M. Armgarth and I. Lundström (Linköping, Sweden)

Oxidation and diffusion in black chrome selective solar absorber coatings . . 95
P. H. Holloway, K. Shanker, G. A. Alexander and L. de Sedas (Gainesville, FL, U.S.A.)

METALLURGICAL AND PROTECTIVE COATINGS

Effect of surface precipitation of titanium carbide on adherence of alumina film on steels . . . . . 107
M. Tosa, Y. Ikeda and K. Yoshihara (Tsukuba, Japan)

The influence of substrate hardness on the response of TiN-coated steels to surface deformation . . . . . 117
J. C. Knight and T. F. Page (Newcastle upon Tyne, U.K.) and I. M. Hutchings (Cambridge, U.K.)

The laser surface melting of aluminium–silicon-based alloys . . . . . 133
P. W. Leech (Clayton, Victoria, Australia)

PREPARATION AND CHARACTERIZATION

Kinetic model of morphological instabilities in chemical vapor deposition . . 141
B. J. Palmer and R. G. Gordon (Cambridge, MA, U.S.A.)

The influence of unsteady state plasma on the properties of a-Si:H films formed by glow discharge–chemical vapour deposition . . . . . 161
K. Hamamoto, H. Ozaki, K. Nakatani, M. Yano, K. Suzuki and H. Okaniwa (Tokyo, Japan)

A spectroscopic study of nickel oxide films on polycrystalline nickel . . . . . 171
S. Mitra, S. R. Tatti and J. P. Stark (Austin, TX, U.S.A.)

Ambient-induced interface reactions and adhesion failure in the Ag/TlBr–TlI system . . . . . 181
S. V. Stolyarova, A. A. Simanovskis, V. N. Kovalev and S. A. Varchenya (Riga, U.S.S.R.)

A thermodynamic and experimental approach to $TaSi_2$ chemical vapour deposition . . . . . 189
E. Blanquet, C. Vahlas, R. Madar (St. Martin d'Heres, France), J. Palleau, J. Torres (Meylan, France) and C. Bernard (St. Martin d'Heres)

A study of electroless nickel coatings, containing low phosphorus . . . . . 207
M. R. Lambert (Parsippany, NJ, U.S.A.) and D. J. Duquette (Troy, NY, U.S.A.)

The influence of rapid thermal processing on the properties of $MoSi_2$ layers formed by using the ion implantation through metal technique . . . . . 225
Th. Gessner, R. Reich, W. Unger and W. Wolke (Karl-Marx-Stadt, G.D.R.)

Doped silicon dioxide films from spin-on solutions . . . . . 231
M. Kuisl (Ulm, F.R.G.)

Crystallization and melting of thin $Bi_xSe_{1-x}$ layers . . . . . 239
H. Atmani, G. Coquerel and C. Vautier (Mont St. Aignan, France)

Minimal spanning tree: a new approach to quantifying the oriented growth of thin films . . . . . 245
C. Dussert, G. Rasigni and A. Llebaria (Marseilles, France)

Properties of hydrogenated amorphous silicon carbide films prepared by plasma-enhanced chemical vapor deposition . . . . . 253
D. Kuhman, S. Grammatica and F. Jansen (Webster, NY, U.S.A.)

Ti/Ni bilayers on silicon: sputter-induced intermixing, rapid thermal annealing and ternary silicide formation . . . . . 263
E. Horache, J. Van Der Spiegel and J. E. Fischer (Philadelphia, PA, U.S.A.)

Structure and properties of metallic Sn–Zn alloy films prepared by plasma-enhanced metalorganic chemical vapor deposition . . . . . 271
T. J. Lin, T. J. O'Keefe and W. J. James (Rolla, MO, U.S.A.)

Ellipsometric investigation of the growth mode of antimony overlayers on GaAs(110) . . . . . 287
R. Strümpler and H. Lüth (Aachen, F.R.G.)

LANGMUIR–BLODGETT AND RELATED FILMS

Formation of polymerized thiophene films by photochemical vapour deposition . . . . . 295
T. Sorita, H. Fujioka, M. Inoue and H. Nakajima (Hyogo, Japan)

Ellipsometric study of the optical anisotropy of lead arachidate Langmuir films . . . . . 305
A. Y. Tronin and A. F. Konstantinova (Moscow, U.S.S.R.)

GENERAL FILM BEHAVIOUR

Effect of V–O barriers in Cr–Si–O/V–O/Al thin film system . . . . . 315
K.-H. Bäther, R. Voigtmann, W. Moldenhauer, G. Zies and H. Schreiber (Dresden, G.D.R.)

A two-dimensional Lennard–Jones lattice gas
I: Ground state structures . . . . . 333
P. Borowski, A. Patrykiejew and S. Sokołowski (Lublin, Poland)

LETTER

The grain growth of $CdS_{0.6}Se_{0.4}$ films . . . . . L187
N. Nishitani, K. Hisamoto and N. Yukami (Osaka, Japan)

AUTHOR INDEX . . . . . 347